

[RE-OXIDATION PROCESS OF SEMICONDUCTOR DEVICE]

Abstract of Disclosure

A re-oxidation process of a semiconductor device is described. A substrate having a stacked structure thereon is provided, wherein the stacked structure includes a polysilicon/tungsten silicide interface. A thin CVD oxide layer is formed on the substrate and the stacked structure with a chemical vapor deposition (CVD) process. Then, an oxidation process is performed to form a thermal oxide layer on the substrate and the stacked structure.